AMORPHOUS AND POLYCRYSTALLINE GROWING METHOD FOR GALLIUM NITRIDE BASED COMPOUND SEMICONDUCTOR

Abstract

The amorphous and polycrystalline structures of a GaN-based semiconductor are grown on the surface of a compound semiconductor layer showing by formation of $In_xAl_yGa_{(1-x-y)}N$ ($0 \leq (x,y) \leq 1.0000$, and $(x+y) \leq 1.0000$). More specified from others, different kinds of the amorphous and polycrystalline structures of the InAlGaN based compound semiconductor layers grown on the surface of the InAlGaN based compound semiconductor can be functionally well significantly, and can be applied together or individually in different band-gap designs for different compound semiconductors.

FIGURE 1